

## Preface

These volumes contain the written papers that were presented at the International Conference on Silicon Carbide and Related Materials 2005 (ICSCRM 2005), which was held in Pittsburgh, Pennsylvania, from September 18-23, 2005. A total of 421 papers, 35 of them invited or plenary, were presented during the conference. There were 652 registered attendees, including 97 students. The size of ICSCRM 2005 was comparable to ICSCRM 1999, the last time the conference was held in the United States, indicating that the rapid growth of ICSCRM during the 1990's has leveled off as the field has matured.

The major chapters of these Proceedings collect papers in the areas of bulk growth of SiC, epitaxial growth of SiC, physical properties and characterization (including theory), processing, and devices. There are three shorter chapters on porous SiC, SiC nanoparticles and nanowires, III-nitrides, and related materials. Impressive progress is reported in all of these chapters.

The success of ICSCRM 2005 is based on the hard work of a large number of people who served on the various committees, as well as the generous financial support of the industrial sponsors. The Editors thank their student assistants Yue (Leo) Ke and Fei Yan from the University of Pittsburgh and Ian Haslebarth and Suzie Harvey from the University of South Florida, who missed most of the conference while serving in the editorial office.

The next conference in this series, ICSCRM 2007, will take place at Lake Biwa Resort, Otsu, Japan, from October 14-19, 2007. The General Co-Chairpersons are Akira Suzuki (Ritsumeikan University) and Hajime Okumura (AIST). Tsunenobu Kimoto (Kyoto University) will be the Proceedings editor. We wish the organizers much success!

Pittsburgh, September, 2005

Robert P. Devaty

David J. Larkin

Stephen E. Saddow